

ABSTRACT OF THE DISCLOSURE

The present invention provides a resist pattern thickening material and the like which can thicken a resist pattern and form a fine space pattern. The resist pattern thickening material contains: a resin; a crosslinking agent; and at least one type selected from cationic surfactants, amphoteric surfactants, and non-ionic surfactants selected from alkoxylate surfactants, fatty acid ester surfactants, amide surfactants, alcohol surfactants, and ethylene diamine surfactants. In a process for forming a resist pattern of the present invention, after a resist pattern is formed, the thickening material is applied onto a surface of the pattern. A process for manufacturing a semiconductor device of the present invention includes: after forming a resist pattern on an underlying layer, applying the thickening material on a surface of the pattern so as to thicken the pattern; and a step of patterning the underlying layer by etching by using the pattern.